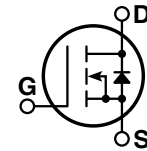


POWER MOS V®




Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.

- Fast Recovery Body Diode
- Lower Leakage
- Faster Switching
- 100% Avalanche Tested
- Popular SOT-227 Package



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT10M07JVFR	UNIT
V_{DSS}	Drain-Source Voltage	100	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	225	Amps
I_{DM}	Pulsed Drain Current ^①	900	
V_{GS}	Gate-Source Voltage Continuous	± 30	Volts
V_{GSM}	Gate-Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	700	Watts
	Linear Derating Factor	5.6	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ^① (Repetitive and Non-Repetitive)	225	Amps
E_{AR}	Repetitive Avalanche Energy ^①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ^④	3600	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu\text{A}$)	100			Volts
$I_{D(on)}$	On State Drain Current ^② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$)	225			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ^② ($V_{GS} = 10V, 0.5 I_{D[Cont.]}$)			0.007	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 5.0\text{mA}$)	2		4	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT10M07JVFR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{iss}	Input Capacitance	V _{GS} = 0V		18000	21600	pF
C _{oss}	Output Capacitance	V _{DS} = 25V		6800	9500	
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		2800	4200	
Q _g	Total Gate Charge ③	V _{GS} = 10V		700	1050	nC
Q _{gs}	Gate-Source Charge	V _{DD} = 0.5 V _{DSS}		130	195	
Q _{gd}	Gate-Drain ("Miller") Charge	I _D = I _D [Cont.] @ 25°C		300	435	
t _{d(on)}	Turn-on Delay Time	V _{GS} = 15V		25	50	ns
t _r	Rise Time	V _{DD} = 0.5 V _{DSS}		60	120	
t _{d(off)}	Turn-off Delay Time	I _D = I _D [Cont.] @ 25°C		80	120	
t _f	Fall Time	R _G = 0.6Ω		20	40	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT	
I _S	Continuous Source Current (Body Diode)			225	Amps	
I _{SM}	Pulsed Source Current ① (Body Diode)			900		
V _{SD}	Diode Forward Voltage ② (V _{GS} = 0V, I _S = -I _D [Cont.])			1.3	Volts	
dv/dt	Peak Diode Recovery dv/dt ⑤			8	V/ns	
t _{rr}	Reverse Recovery Time (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C		150	250	ns
		T _j = 125°C		250	500	
Q _{rr}	Reverse Recovery Charge (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C		0.9		μC
		T _j = 125°C		2.5		
I _{RRM}	Peak Recovery Current (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C		12		Amps
		T _j = 125°C		20		

THERMAL/PACKAGE CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R _{θJC}	Junction to Case			0.18	°C/W
R _{θJA}	Junction to Ambient			40	
V _{isolation}	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations.			13	lb•in

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
- ② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%
- ③ See MIL-STD-750 Method 3471
- ④ Starting T_j = +25°C, L = 142μH, R_G = 25Ω, Peak I_L = 225A

APT Reserves the right to change, without notice, the specifications and information contained herein.

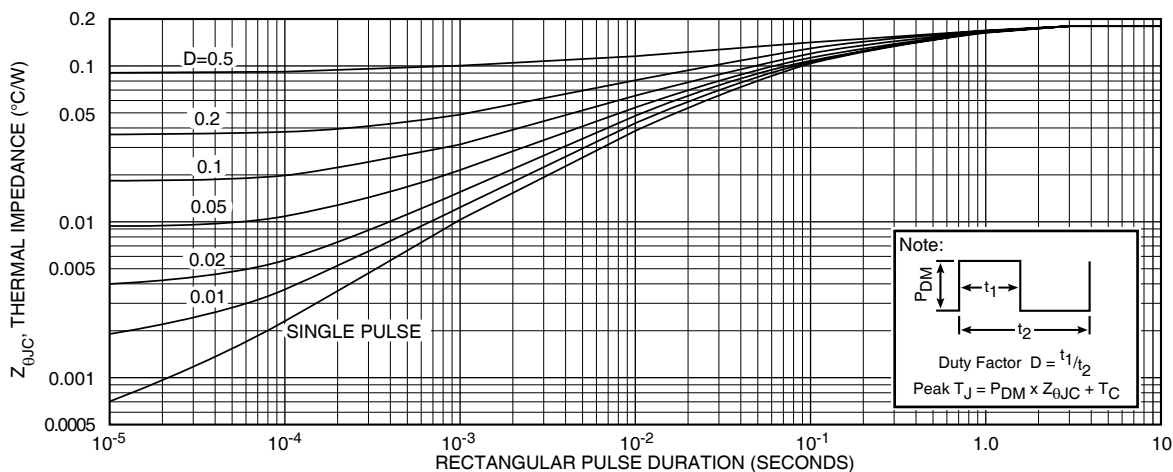


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

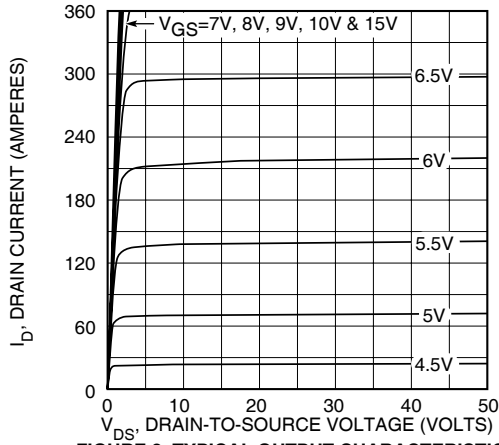


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

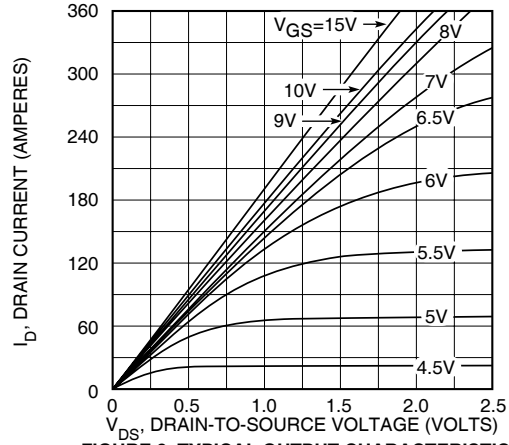


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

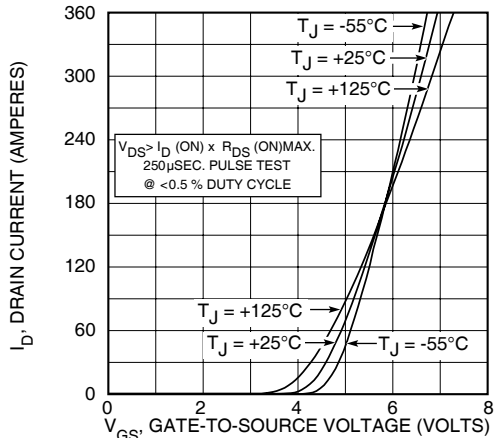


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

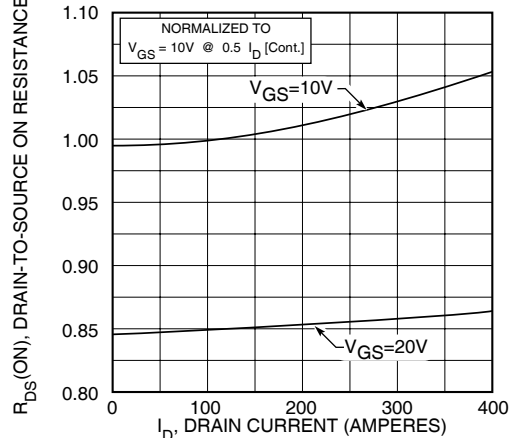


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

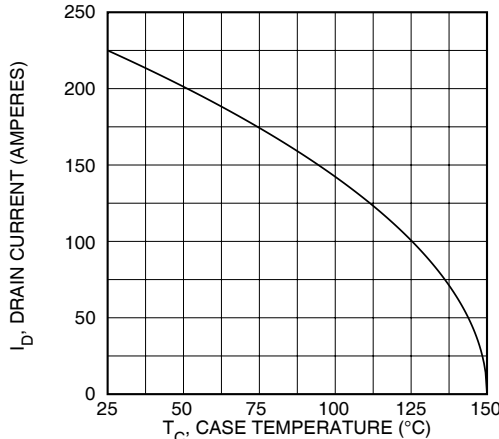


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

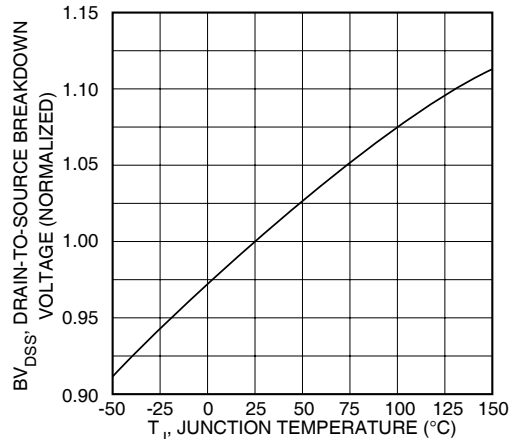


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

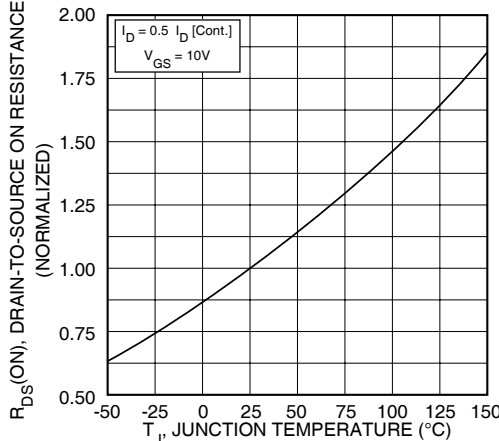


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

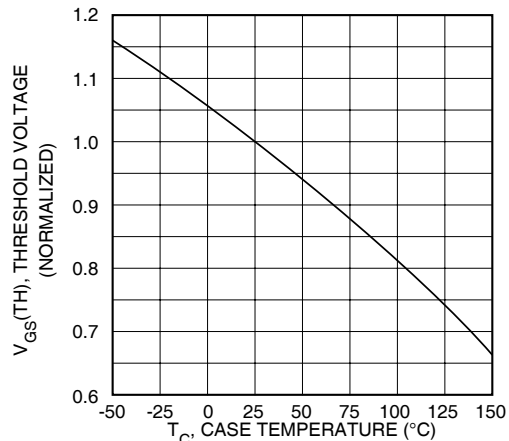


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

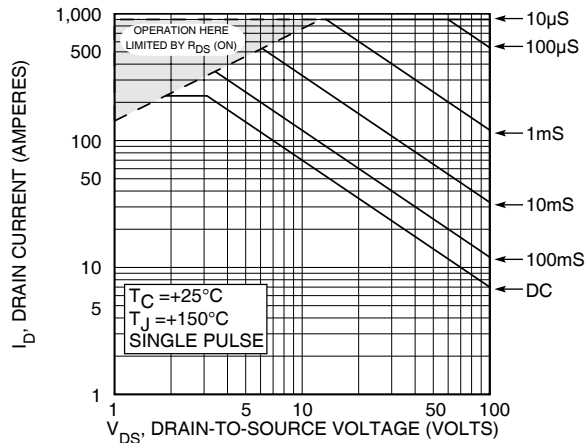


FIGURE 10, MAXIMUM SAFE OPERATING AREA

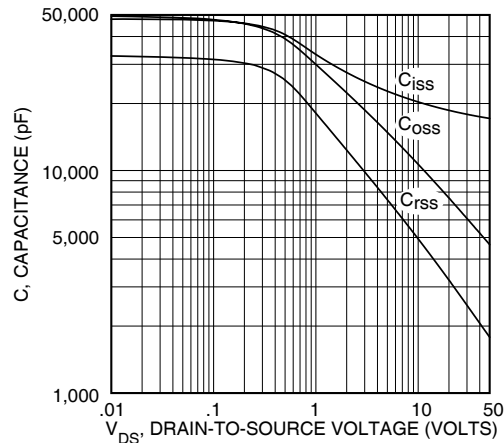


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

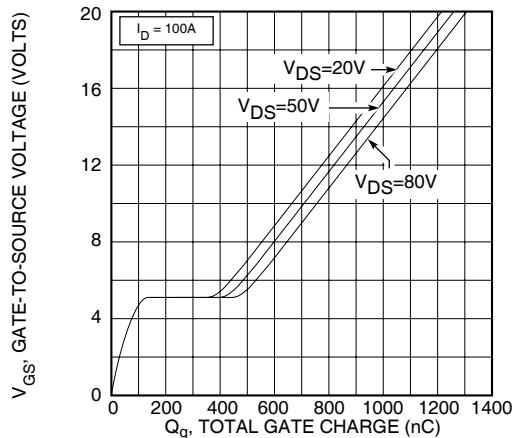


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

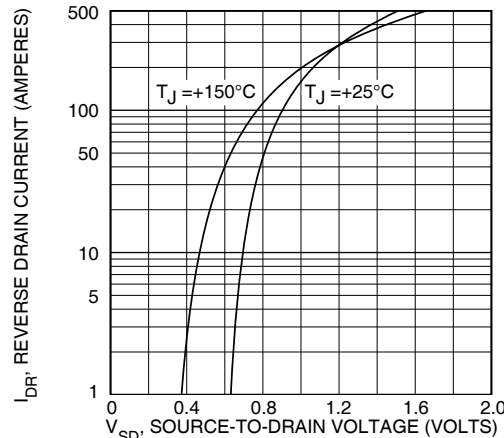
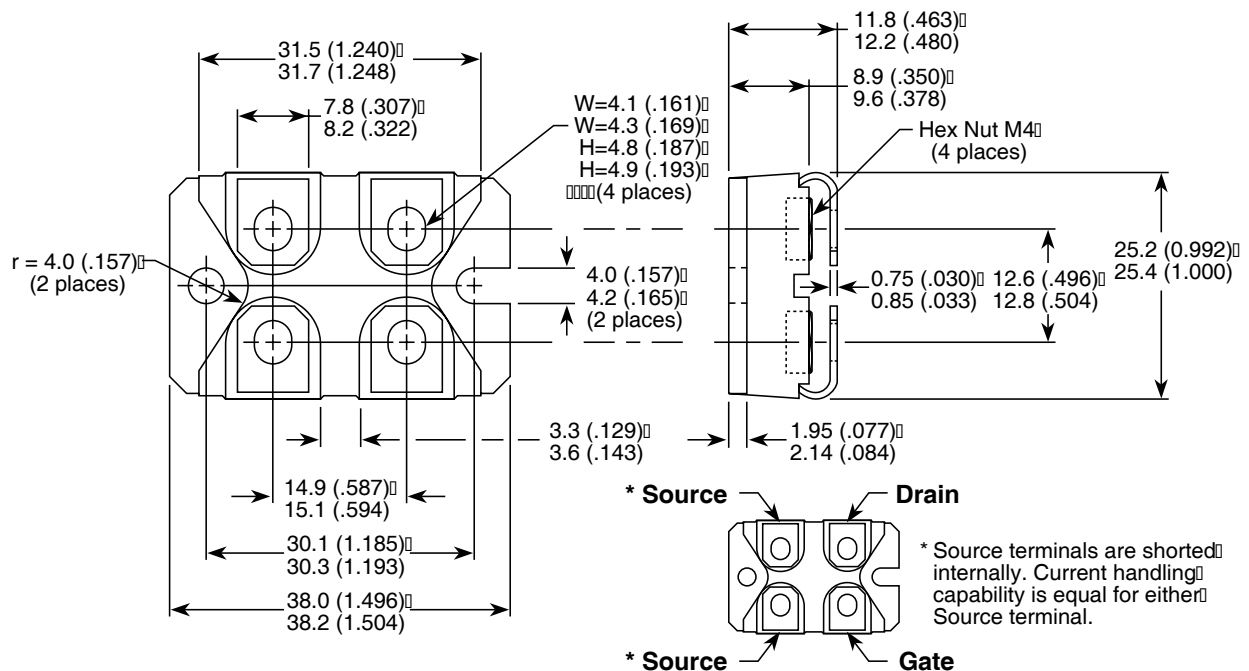


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

* Source terminals are shorted internally. Current handling capability is equal for either Source terminal.

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UL Recognized File No. E145592

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522

5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.